

P-Channel 40 V (D-S) MOSFET



RoHS
COMPLIANT

| PRODUCT SUMMARY | | | |
|---------------------|---------------------------------|---------------------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (mΩ)(Typ.) | I _D (A) ^a | Q _g (Typ.) |
| - 40 | 38 at V _{GS} = - 10 V | - 30 | 18 nC |
| | 60 at V _{GS} = - 4.5 V | | |

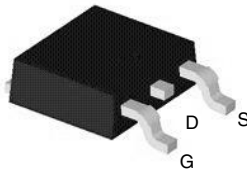
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Excellent package for good heat dissipation

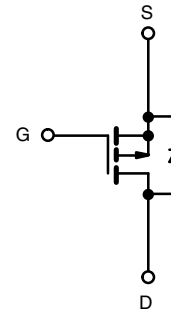
APPLICATIONS

- Load switch
- PWM application

TO-252 Pin Configuration



Top View



P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | |
|---|-------------------------|-----------------------------------|-------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V _{DS} | - 40 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _C = 25 °C | I _D | - 30 | A |
| | T _C = 100 °C | | - 20 | |
| Pulsed Drain Current ^b | | I _{DM} | - 115 | |
| Single Pulse Avalanche Energy | | E _{AS} | 100 | mJ |
| Maximum Power Dissipation ^c | T _C = 25 °C | P _D | 50 | W |
| | T _C = 100 °C | | 20 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-Ambient | PCB mount ^d | R _{thJA} | 50 | °C/W |
| Junction-to-Case | | R _{thJC} | 2.5 | |

Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P_d is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{thJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

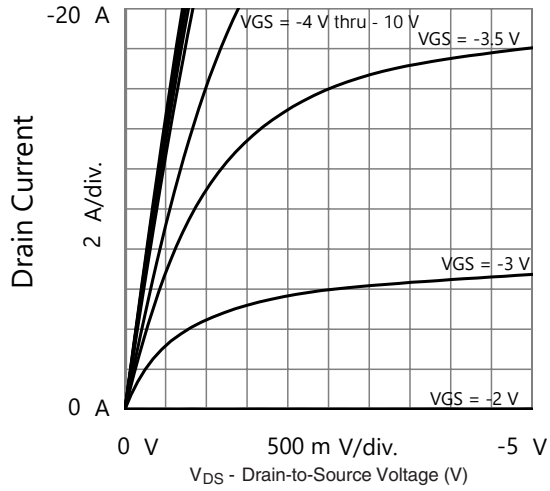
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|--------------|---|------|------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | - 40 | | | V |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | - 1 | | 3 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$ | | | - 1 | μA |
| | | $V_{DS} = -32\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | - 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$ | - 30 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}, I_D = -10\text{ A}$ | | 38 | 47 | m Ω |
| | | $V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$ | | 60 | 72 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -5\text{ V}, I_D = -10\text{ A}$ | | 25 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 950 | | pF |
| Output Capacitance | C_{oss} | | | 77 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 68 | | |
| Total Gate Charge | Q_g | $V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$ | | 18 | | nC |
| Gate-Source Charge | Q_{gs} | | | 5 | | |
| Gate-Drain Charge | Q_{gd} | | | 4 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 6.6 | | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -20\text{ V}, I_D = -10\text{ A},$ $V_{GEN} = -10\text{ V}, R_g = 3\text{ }\Omega$ | | 6 | | ns |
| Rise Time | t_r | | | 8 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 44 | | |
| Fall Time | t_f | | | 41 | | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | | - 30 | A |
| Pulse Diode Forward Current ^a | I_{SM} | | | | - 115 | |
| Body Diode Voltage | V_{SD} | $I_S = -1\text{ A}$ | | | - 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = -10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 25 | | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | | 14.5 | |

Notes:

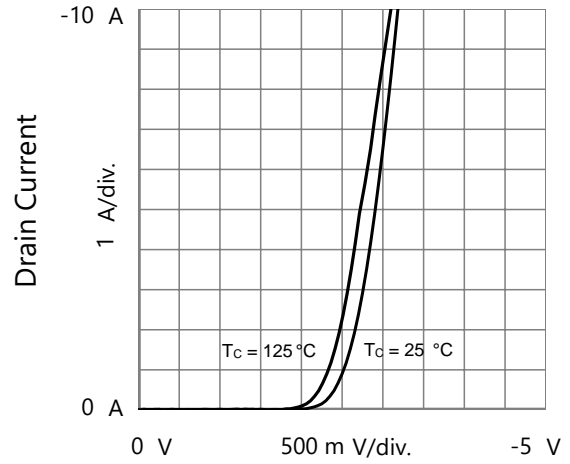
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

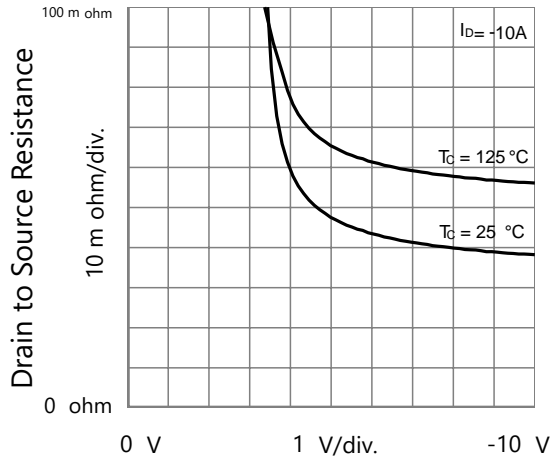
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics

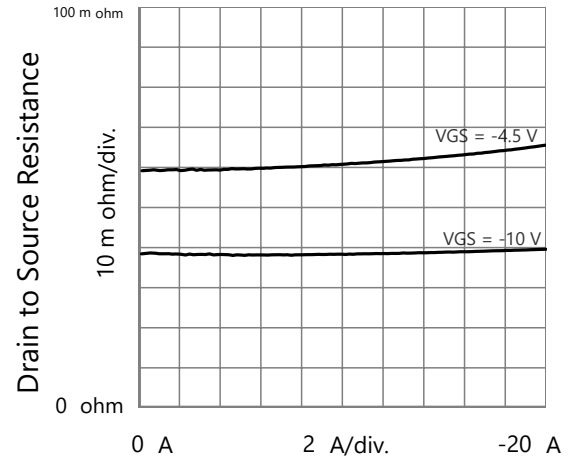


Transfer Characteristics



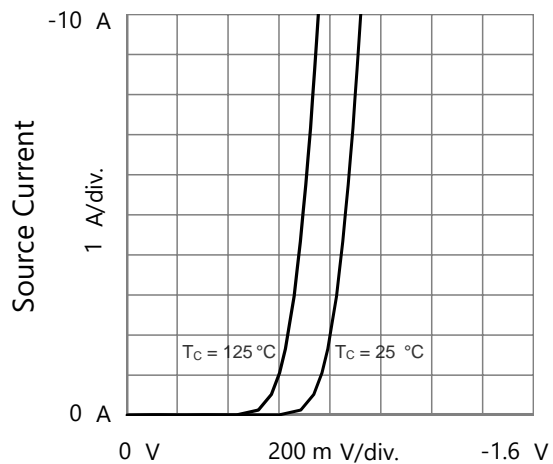
Gate to Source Voltage

Drain to Source Resistance vs. Gate to Source Voltage



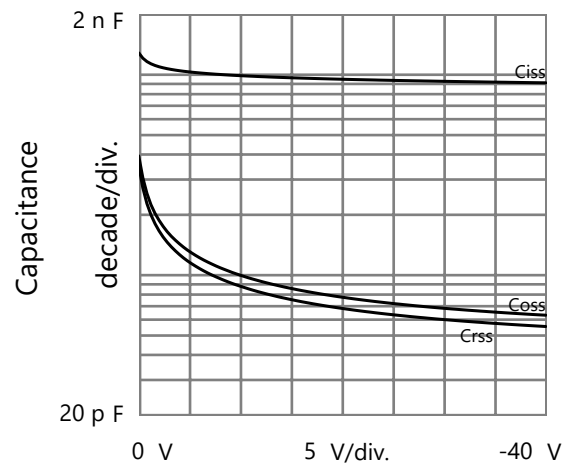
Drain Current

Drain to Source Resistance vs. Drain Current



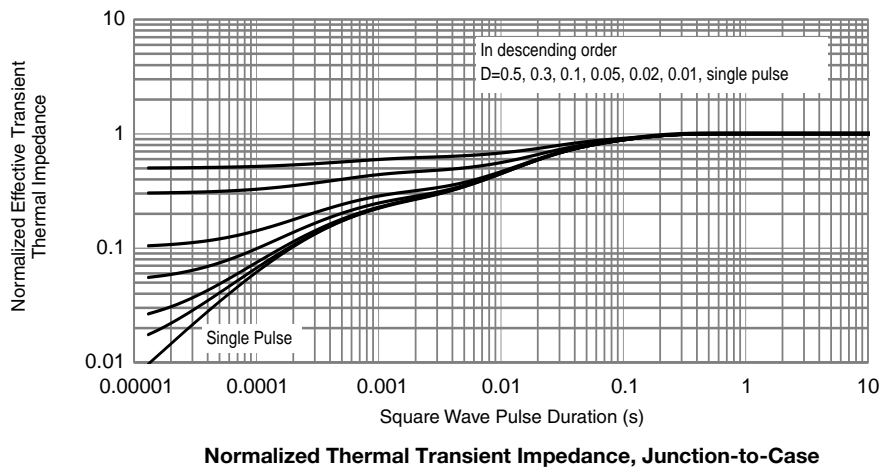
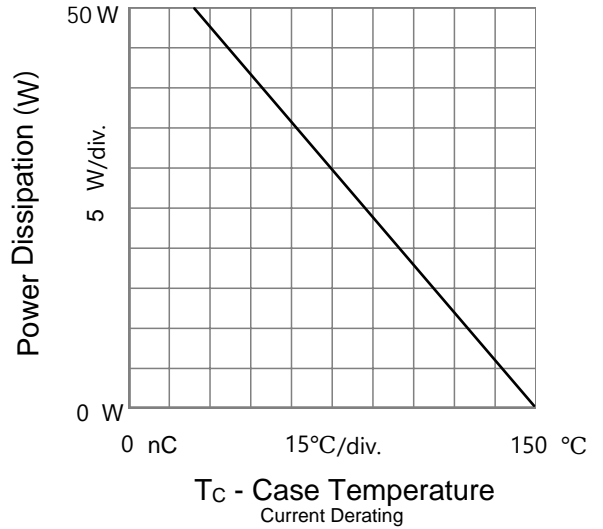
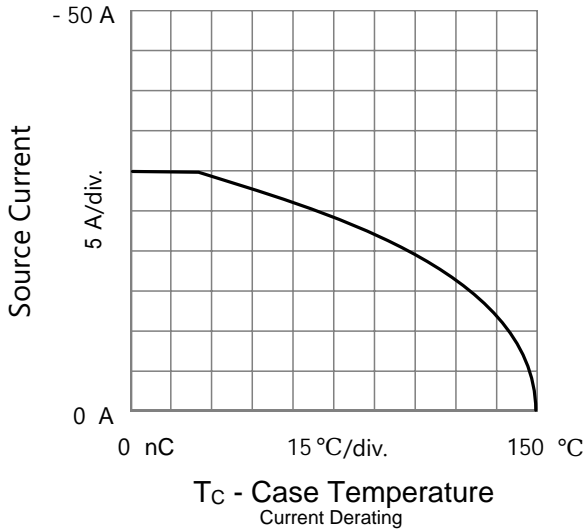
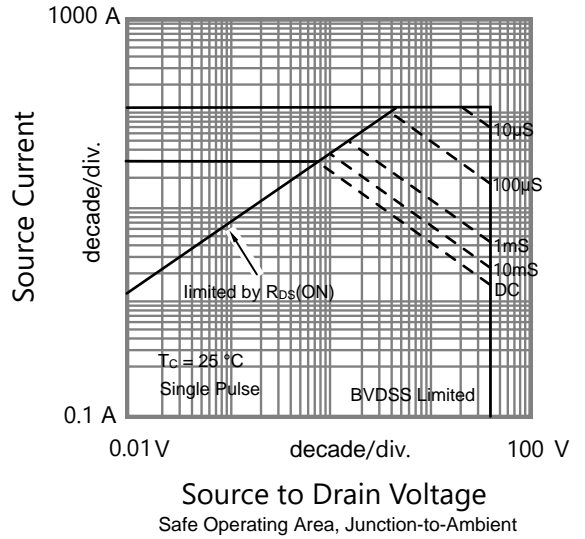
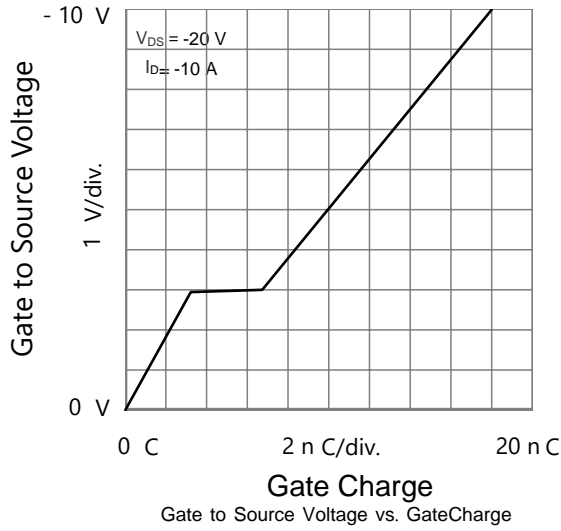
Source to Drain Voltage

Body Diode Forward Characteristics

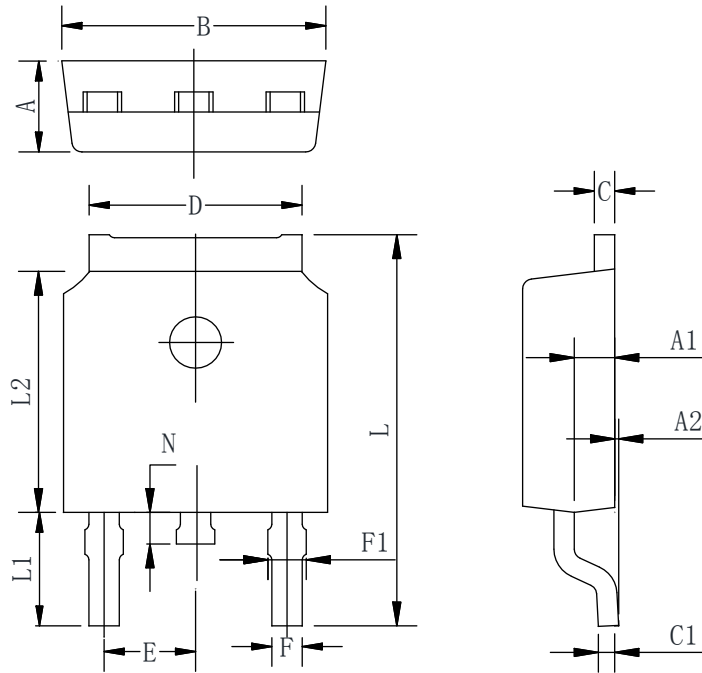


Drain to Source Voltage Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| Symbol | Min | Typ | Max |
|--------|-----------|------|-------|
| A | 2.10 | 2.30 | 2.50 |
| A1 | 0.88 | 1.01 | 1.16 |
| A2 | 0.00 | 0.15 | 0.28 |
| B | 6.40 | 6.60 | 6.80 |
| C | 0.42 | 0.50 | 0.63 |
| C1 | 0.42 | 0.50 | 0.63 |
| D | 5.08 | 5.32 | 5.65 |
| E | 2.286 TYP | | |
| F | 0.63 | 0.76 | 0.89 |
| F1 | 0.64 | 0.86 | 1.08 |
| L | 9.30 | 9.90 | 10.80 |
| L1 | 2.4 | 2.8 | 3.6 |
| L2 | 5.90 | 6.10 | 6.55 |
| N | 0.57 | 0.80 | 1.05 |

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